

Abstract of the Disclosure:

The present invention provides a new backside treatment of the wafer. Trenches are cut into the top surface of the wafer by sawing or etching, and after grinding the wafer from the bottom side, a protective material is applied as a surface layer to the bottom surface while filling the trenches with this material. The material is hardened in order to accomplish the sawing process. In another embodiment of the present method, a double foil layer is applied to the rear side of the wafer including a mounting tape and a protective layer facing the wafer rear side.

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